

# PolarHV™ HiPerFET Power MOSFET

N-Channel Enhancement Mode  
Avalanche Rated  
Fast Intrinsic Diode

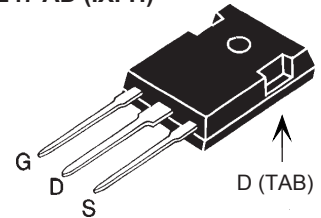
**IXFH 30N50P**  
**IXFT 30N50P**  
**IXFV 30N50P**  
**IXFV 30N50PS**

$V_{DSS} = 500 \text{ V}$   
 $I_{D25} = 30 \text{ A}$   
 $R_{DS(on)} \leq 200 \text{ m}\Omega$   
 $t_{rr} \leq 200 \text{ ns}$

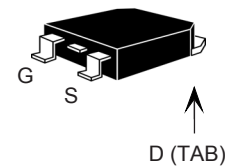


Symbol	Test Conditions	Maximum Ratings	
$V_{DSS}$	$T_J = 25^\circ\text{C to } 150^\circ\text{C}$	500	V
$V_{DGR}$	$T_J = 25^\circ\text{C to } 150^\circ\text{C}; R_{GS} = 1 \text{ M}\Omega$	500	V
$V_{GSS}$	Continuous	$\pm 30$	V
$V_{GSM}$	Transient	$\pm 40$	V
$I_{D25}$	$T_C = 25^\circ\text{C}$	30	A
$I_{DM}$	$T_C = 25^\circ\text{C}$ , pulse width limited by $T_{JM}$	75	A
$I_{AR}$	$T_C = 25^\circ\text{C}$	30	A
$E_{AR}$	$T_C = 25^\circ\text{C}$	40	mJ
$E_{AS}$	$T_C = 25^\circ\text{C}$	1.2	J
$dv/dt$	$I_S \leq I_{DM}$ , $di/dt \leq 100 \text{ A}/\mu\text{s}$ , $V_{DD} \leq V_{DSS}$ , $T_J \leq 150^\circ\text{C}$ , $R_G = 5 \Omega$	10	V/ns
$P_D$	$T_C = 25^\circ\text{C}$	460	W
$T_J$		-55 ... +150	$^\circ\text{C}$
$T_{JM}$		150	$^\circ\text{C}$
$T_{stg}$		-55 ... +150	$^\circ\text{C}$
$T_L$	1.6 mm (0.062 in.) from case for 10 s	300	$^\circ\text{C}$
$T_{SOLD}$	Plastic body for 10 s	260	$^\circ\text{C}$
$M_d$	Mounting torque (TO-247, TO-3P)	1.13/10	Nm/lb.in
$F_c$	Mounting force (PLUS220, PLUS220SMD)	11 65/2.5 15	N/lb.
Weight	PLUS220, PLUS220SMD	4	g
	TO-268	5	g
	TO-247	6	g

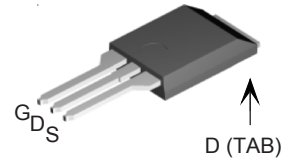
TO-247 AD (IXFH)



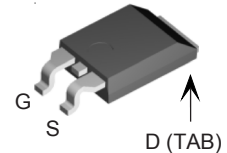
TO-268 (IXFT)



PLUS220 (IXFV)



PLUS220 SMD(IXFV..S)



G = Gate      D = Drain  
S = Source    TAB = Drain

Symbol	Test Conditions ( $T_J = 25^\circ\text{C}$ , unless otherwise specified)	Characteristic Values		
		Min.	Typ.	Max.
$BV_{DSS}$	$V_{GS} = 0 \text{ V}$ , $I_D = 250 \mu\text{A}$	500		V
$V_{GS(th)}$	$V_{DS} = V_{GS}$ , $I_D = 4 \text{ mA}$	3.0		5.0 V
$I_{GSS}$	$V_{GS} = \pm 30 \text{ V}$ , $V_{DS} = 0 \text{ V}$			$\pm 100 \text{ nA}$
$I_{DSS}$	$V_{DS} = V_{DSS}$ $V_{GS} = 0 \text{ V}$ $T_J = 125^\circ\text{C}$			25 $\mu\text{A}$
				750 $\mu\text{A}$
$R_{DS(on)}$	$V_{GS} = 10 \text{ V}$ , $I_D = 0.5 I_{D25}$ Pulse test, $t \leq 300 \mu\text{s}$ , duty cycle $d \leq 2\%$	165	200	$\text{m}\Omega$

### Features

- International standard packages
- Unclamped Inductive Switching (UIS) rated
- Low package inductance
  - easy to drive and to protect

### Advantages

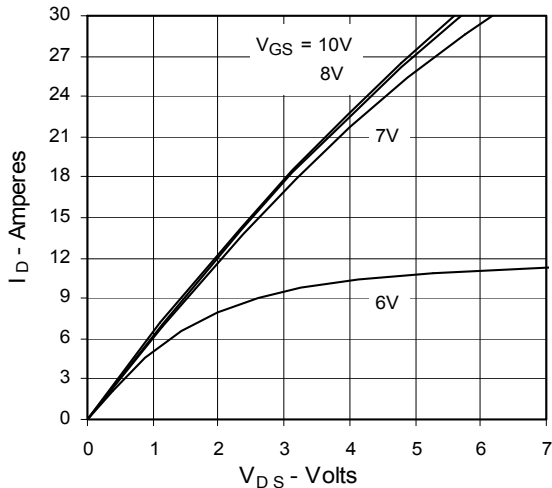
- Easy to mount
- Space savings
- High power density

Symbol	Test Conditions	Characteristic Values		
		(T <sub>J</sub> = 25°C, unless otherwise specified)		
		Min.	Typ.	Max.
<b>g<sub>fs</sub></b>	V <sub>DS</sub> = 20 V; I <sub>D</sub> = 0.5 I <sub>D25</sub> , pulse test	17	27	S
<b>C<sub>iss</sub></b>	V <sub>GS</sub> = 0 V, V <sub>DS</sub> = 25 V, f = 1 MHz		4150	pF
<b>C<sub>oss</sub></b>			445	pF
<b>C<sub>rss</sub></b>			28	pF
<b>t<sub>d(on)</sub></b>	V <sub>GS</sub> = 10 V, V <sub>DS</sub> = 0.5 V <sub>DSS</sub> , I <sub>D</sub> = 0.5 I <sub>D25</sub> R <sub>G</sub> = 5 Ω (External)		25	ns
<b>t<sub>r</sub></b>			24	ns
<b>t<sub>d(off)</sub></b>			82	ns
<b>t<sub>f</sub></b>			24	ns
<b>Q<sub>g(on)</sub></b>	V <sub>GS</sub> = 10 V, V <sub>DS</sub> = 0.5 V <sub>DSS</sub> , I <sub>D</sub> = 0.5 I <sub>D25</sub>		70	nC
<b>Q<sub>gs</sub></b>			27	nC
<b>Q<sub>gd</sub></b>			22	nC
<b>R<sub>thJC</sub></b>				0.27°C/W
<b>R<sub>thCs</sub></b>	(TO-247, PLUS220)		0.21	°C/W

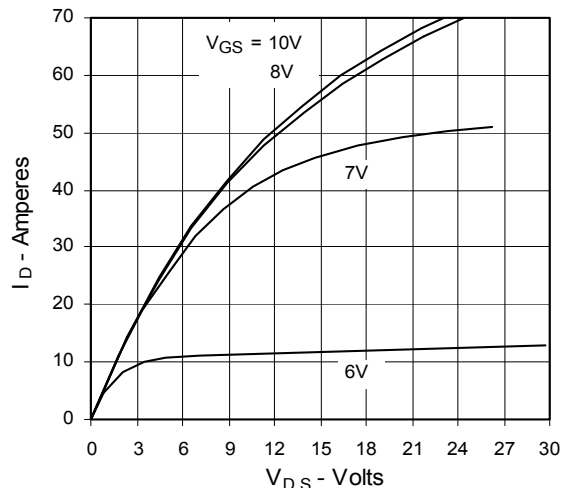
Source-Drain Diode		Characteristic Values		
		(T <sub>J</sub> = 25°C, unless otherwise specified)		
Symbol	Test Conditions	Min.	Typ.	Max.
<b>I<sub>S</sub></b>	V <sub>GS</sub> = 0 V			30 A
<b>I<sub>SM</sub></b>	Repetitive			90 A
<b>V<sub>SD</sub></b>	I <sub>F</sub> = I <sub>S</sub> , V <sub>GS</sub> = 0 V, Pulse test, t ≤ 300 μs, duty cycle d ≤ 2 %			1.5 V
<b>t<sub>rr</sub></b>	I <sub>F</sub> = 25 A; -di/dt = 100 A/μs			200 ns
<b>I<sub>RM</sub></b>	V <sub>R</sub> = 100 V; V <sub>GS</sub> = 0 V		6	A
<b>Q<sub>RM</sub></b>			0.6	μC

### Characteristic Curves

**Fig. 1. Output Characteristics**  
@ 25°C



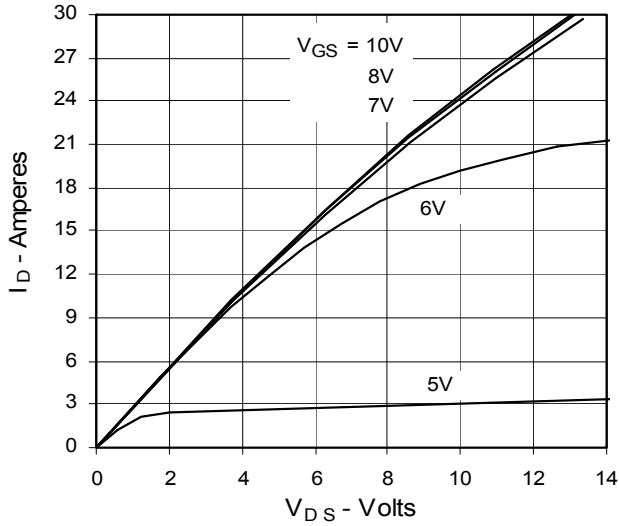
**Fig. 2. Extended Output Characteristics**  
@ 25°C



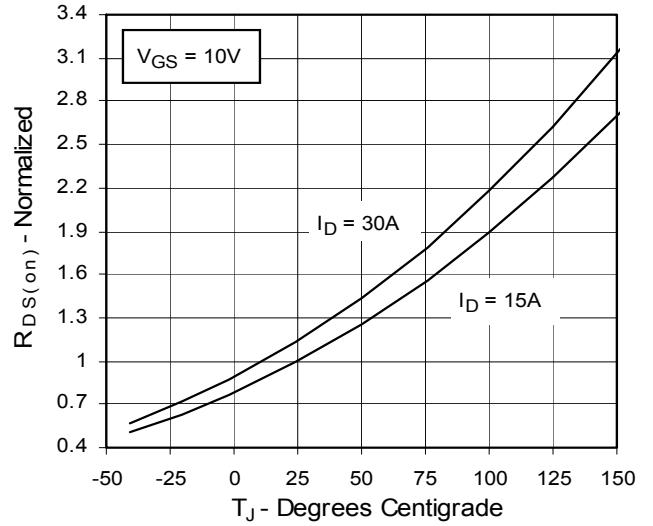
IXYS reserves the right to change limits, test conditions, and dimensions.

IXYS MOSFETs and IGBTs are covered by 4,835,592 4,931,844 5,049,961 5,237,481 6,162,665 6,404,065 B1 6,683,344 6,727,585  
 one or more of the following U.S. patents: 4,850,072 5,017,508 5,063,307 5,381,025 6,259,123 B1 6,534,343 6,710,405B2 6,759,692  
 4,881,106 5,034,796 5,187,117 5,486,715 6,306,728 B1 6,583,505 6,710,463 6,771,478 B2

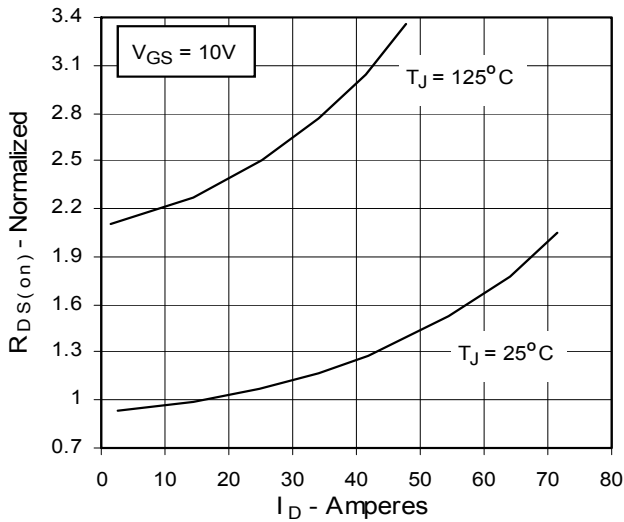
**Fig. 3. Output Characteristics  
@ 125°C**



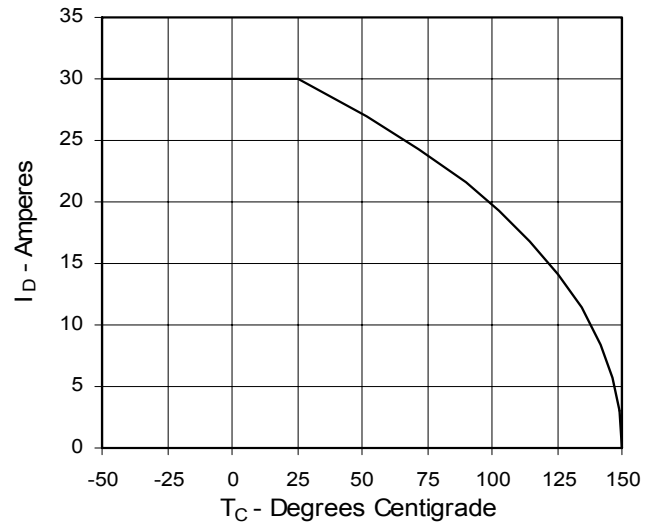
**Fig. 4.  $R_{DS(on)}$  Normalized to 0.5  $I_{D25}$   
Value vs. Junction Temperature**



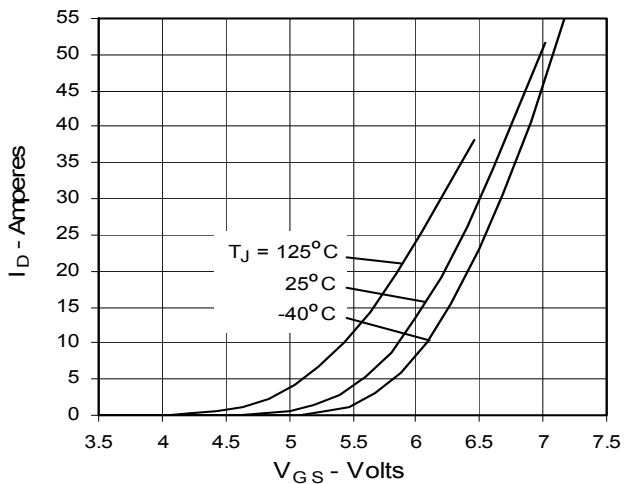
**Fig. 5.  $R_{DS(on)}$  Normalized to  
0.5  $I_{D25}$  Value vs.  $I_D$**



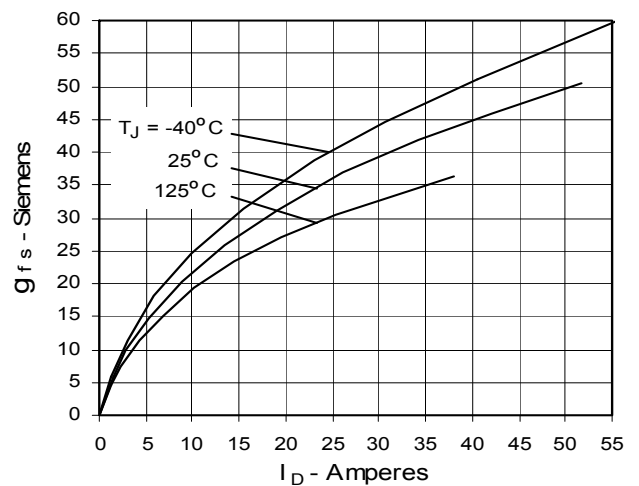
**Fig. 6. Drain Current vs. Case  
Temperature**



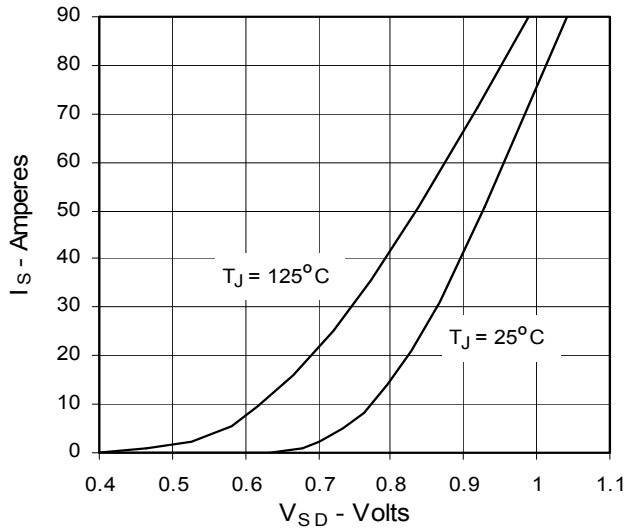
**Fig. 7. Input Admittance**



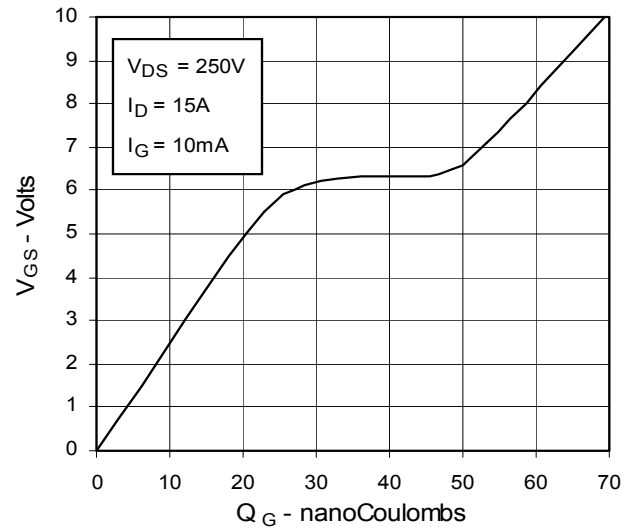
**Fig. 8. Transconductance**



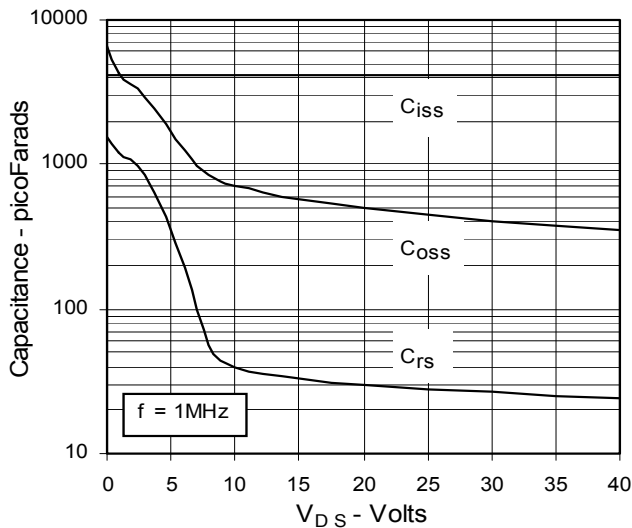
**Fig. 9. Source Current vs. Source-To-Drain Voltage**



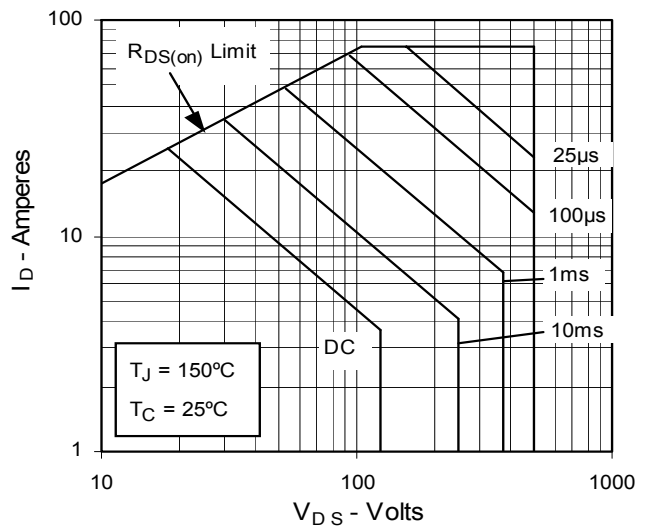
**Fig. 10. Gate Charge**



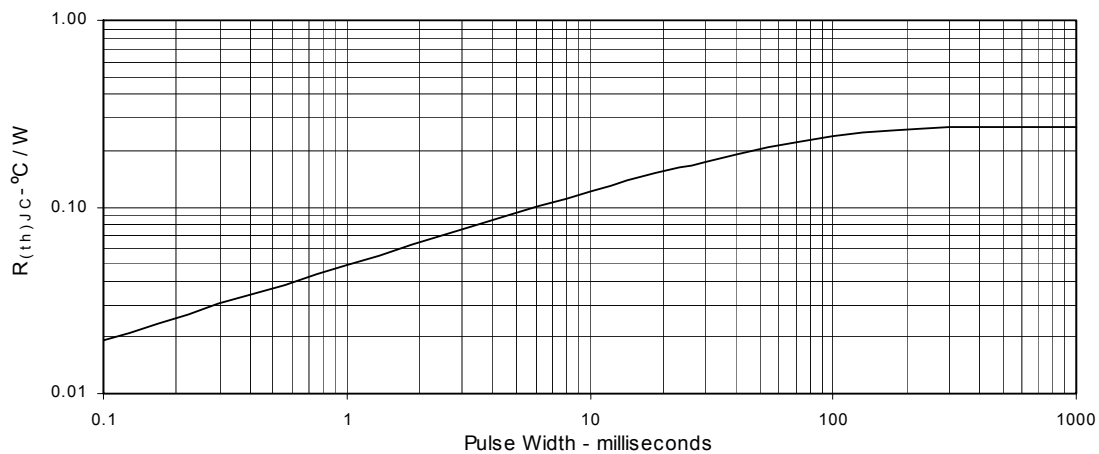
**Fig. 11. Capacitance**



**Fig. 12. Forward-Bias Safe Operating Area**



**Fig. 13. Maximum Transient Thermal Resistance**







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